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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Isamu Kobori et al.
Serial No. : 10/623,581
Filed : July 22, 2003
Title : METHOD OF MANUFACTURING A SEMICONDUCTOR METHOD OF MANUFACTURING A THIN-FILM TRANSISTOR AND THIN-FILM TRANSISTOR

Art Unit : 2811
Examiner : Stanetta Isaac

MAIL STOP AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REPLY TO ACTION OF JULY 13, 2005

Claims 16-36 are pending in this application, with claims 16, 22, and 28 being independent.

The specification has been reviewed and no further minor errors have been found.

Independent claims 16, 22 and 28, along with their dependent claims 17, 19-21, 23, 25-27, 29-31 and 33-36, have been rejected as being unpatentable over Matsumoto (U.S. Patent No. 5,396,084) in view of Iwanaga (U.S. Patent No. 5,932,484). Applicants respectfully traverse this rejection.

Claims 16, 22 and 28 each recite a method of forming an "*active matrix circuit*" that includes "forming an interlayer insulating film comprising a silicon nitride layer and a silicon oxide layer over said semiconductor layer by plasma CVD, said *silicon nitride layer and said silicon oxide layer formed over said gate electrode* and said semiconductor layer" (emphasis added). Applicants request reconsideration and withdrawal of the rejection of claims 16, 22 and 28, and their dependent claims, because neither Matsumoto, Iwanaga, nor any proper combination of the two describes or suggests forming an *active matrix circuit* by forming an interlayer insulating film that includes a silicon nitride layer and a silicon oxide layer over the recited gate electrode.

In the "Response to Arguments" section of the Office Action, the Examiner states:

> The Examiner takes the position that the method of forming an active matrix circuit comprising a transistor, where Matsumoto teaches the first interlayer insulating film to be made of silicon oxide or silicon nitride and the second interlayer insulating film be also made of silicon oxide or silicon nitride, and both interlayer insulating films are formed by a plasma CVD method, would include an interlayer insulating film that has